

2N5609

Silicon PNP Transistors

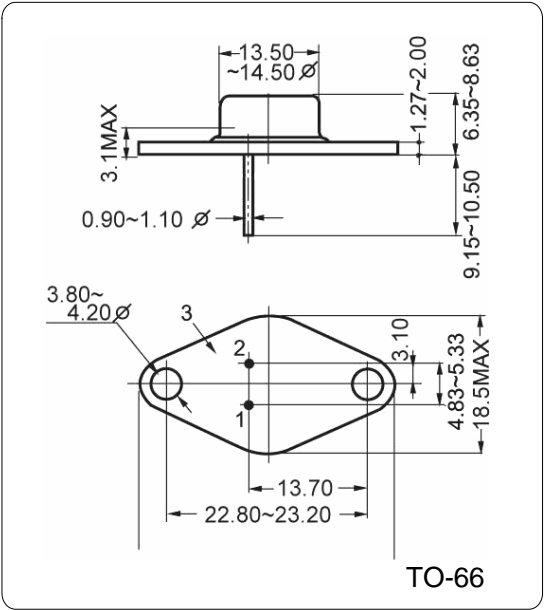


◆ Features

- With TO-66 package
- Designed for use as high-frequency drivers in audio amplifier

◆ Absolute Maximum Ratings $T_c=25^{\circ}\text{C}$

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	80	V
V_{CEO}	Collector to emitter voltage	80	V
V_{EBO}	Emitter to base voltage	5.0	V
I_{CP}	Peak collector current		A
I_C	Collector current	5.0	A
P_C	Collector power dissipation	25	W
T_j	Junction temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-55~150	$^{\circ}\text{C}$



◆ Electrical Characteristics $T_c=25^{\circ}\text{C}$

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{CBO}	Collector-base cut-off current	$V_{CB}=80\text{V}; I_E=0$		10	μA
I_{EBO}	Emitter-base cut-off current	$V_{EB}=5\text{V}; I_C=0$		10	μA
I_{CEO}	Collector-emitter cut-off current				
V_{CBO}	Collector-base breakdown voltage				
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10\text{mA}; I_B=0$	80		V
V_{EBO}	Emitter-base breakdown voltage				
$V_{CEsat-1}$	Collector-emitter saturation voltages	$I_C=1\text{A}; I_B=0.1\text{A}$		0.5	V
$V_{CEsat-2}$	Collector-emitter saturation voltages				
$V_{CEsat-3}$	Collector-emitter saturation voltages				
$V_{CEsat-4}$	Collector-emitter saturation voltages				
h_{FE-1}	Forward current transfer ratio	$I_C=2.5\text{A}; V_{CE}=5\text{V}$	70	200	
h_{FE-2}	Forward current transfer ratio				
h_{FE-3}	Forward current transfer ratio				
h_{FE-4}	Forward current transfer ratio				
$V_{BE(sat)1}$	Base-emitter saturation voltages	$I_C=1\text{A}; V_{CE}=2\text{V}$		1.0	V
$V_{BE(sat)2}$	Base-emitter saturation voltages				
$V_{BE(sat)3}$	Base-emitter saturation voltages				
f_T	Transition frequency at $f = 1\text{MHz}$				
t_f	Fall time				
t_s	Turn-off storage time				